

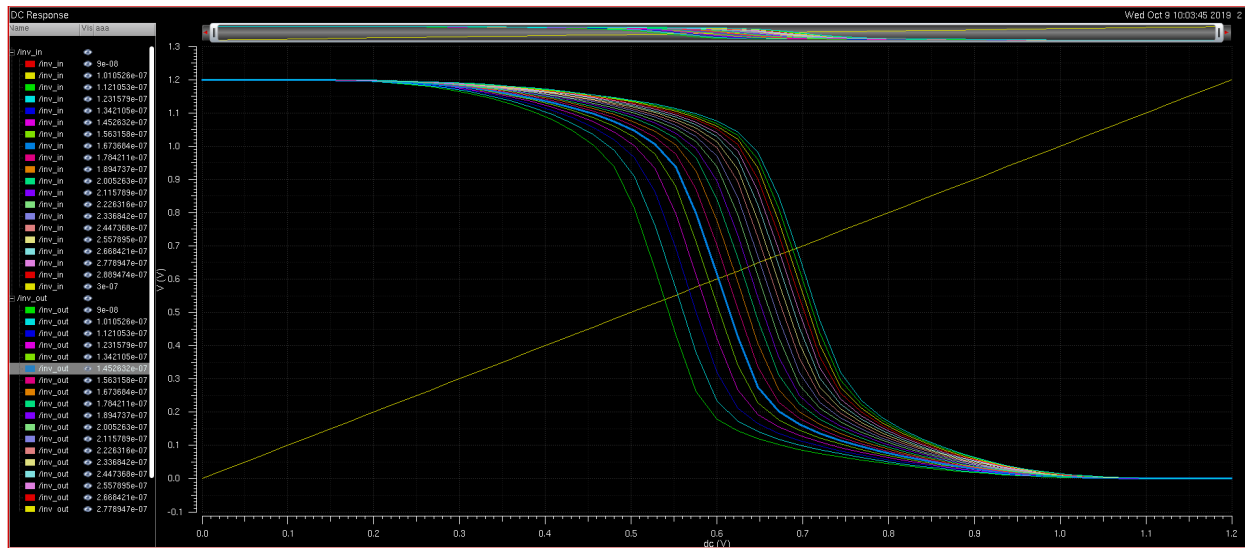
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Lab 1 Results

Schematic View

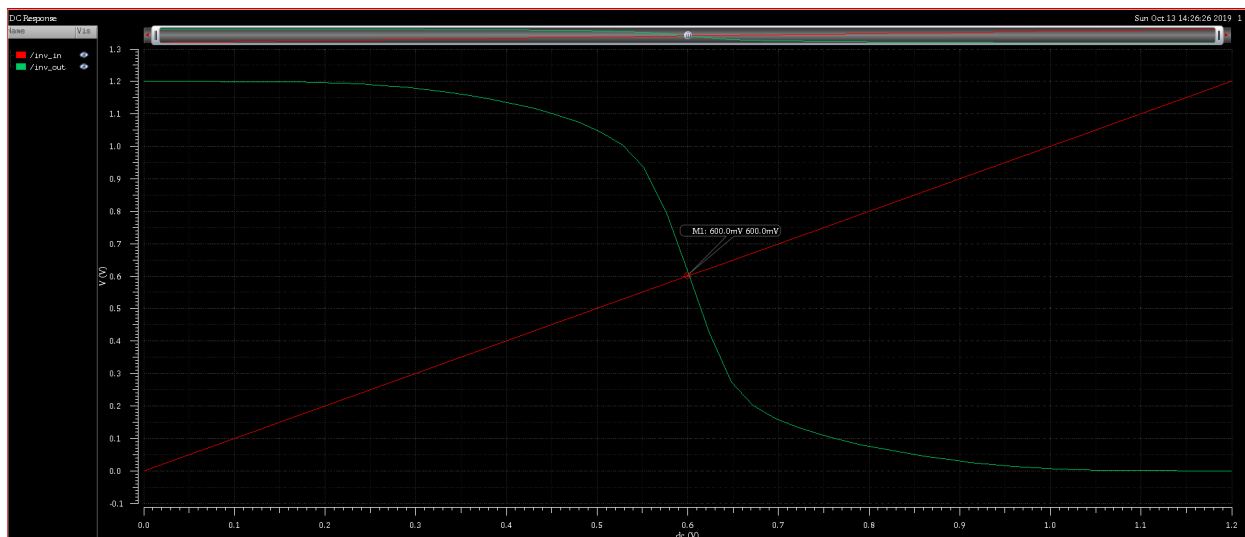




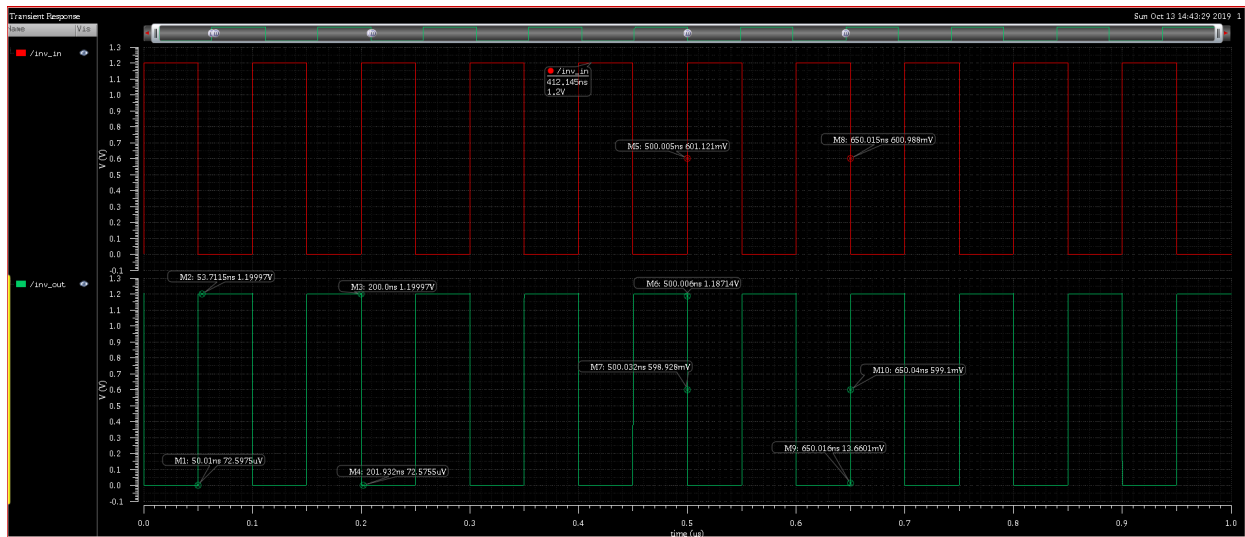
Chosen PMOS channel width

Sweeping from 90nm -> 300nm (step = 10nm), The chosen PMOS channel width is 145nm (shown in [Schematic View](#))

Final DC simulation for chosen PMOS channel width



Final transient simulation result



Timing information extracted from transient simulation

Sim type	t _r	t _f	t _p
Front end sim	3.7015ns	1.932ns	0.026ns

Assuming the rise and fall times are usually measured between the 0% and 100% levels:

$$t_r = 53.7115 - 50.01 = 3.7015ns$$

$$t_f = 201.932 - 200.00 = 1.932ns$$

$$t_{pdf} = 500.032 - 500.005 = 0.027ns$$

$$t_{pdr} = 650.04 - 650.015 = 0.025ns$$

$$t_p = (t_{pdf} + t_{pdr})/2 = 0.026ns$$